

**Analysis of deep level centers in GaAs pin-diode structures**

**Korolkov, Oleg; Toompuu, Jana; Rang, Toomas** Elektronika ir elektrotehnika = Electronics and electrical engineering 2013 / [4 p. ] : ill <https://doi.org/10.5755/j01.eee.19.10.5903> Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

**Investigation of deep level centers in i- and n-layers of GaAs pin-diodes**

**Toompuu, Jana; Korolkov, Oleg; Sleptšuk, Natalja; Rang, Toomas** BEC 2014 : 2014 14th Biennial Baltic Electronics Conference : proceedings of the 14th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 6-8, 2014, Tallinn, Estonia 2014 / p. 25-28 : ill

**Method of samples preparation intended for research of deep centers in i-, n-, and p-layers of GaAs p<sup>+</sup>-pin-n<sup>+</sup> structures and result of analysis**

**Toompuu, Jana; Sleptšuk, Natalja; Korolkov, Oleg; Rang, Toomas** BEC 2016 : 2016 15th Biennial Baltic Electronics Conference : proceedings of the 15th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 3-5, 2016, Tallinn, Estonia 2016 / p. 35-38 : ill [http://www.ester.ee/record=b2150914\\*est](http://www.ester.ee/record=b2150914*est)